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Substitute for form 1449A/PTO **INFORMATION DISCLOSURE STATEMENT BY APPLICANT** *(Use as many sheets as necessary)*	*Complete if Known* Application Number: 10/755,042 Filing Date: January 9, 2004 First Named Inventor: **MOU-SHIUNG LIN** Art Unit: 2815 Examiner Name: **JEROME JACKSON, JR.**
Sheet **1** of **3**	Attorney Docket No: 085027-0104

US PATENT DOCUMENTS

Examiner Initial *	Cite No	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or RelevantFigures Appear
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		NONE				

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No [1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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